

N-channel TrenchMOS logic level FET Rev. 02 — 9 February 2011

Product data sheet

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data						
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	46	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	157	W
Static ch	aracteristics					
R _{DSon} drain-source on-state	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	22	27	mΩ	
	resistance	$V_{GS} = 5 V; I_D = 25 A;$ $T_j = 25 °C; see Figure 6;see Figure 7$	-	24	29	mΩ

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Table 1.	Quick reference da	tacontinued					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanch	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 46 \text{ A}; V_{sup} \leq 100 \text{ V}; \\ R_{GS} &= 50 \Omega; V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $		-	-	152	mJ
Dynamic	Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 80 V; T _j = 25 °C; see <u>Figure 8</u>		-	13	-	nC

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9629-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		5, (
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-15	15	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	46	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	-	32	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>	-	186	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	157	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	46	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	186	А
Avalanche I	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 46 \; A; \; V_{sup} \leq 100 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = 5 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped \end{array}$	-	152	mJ

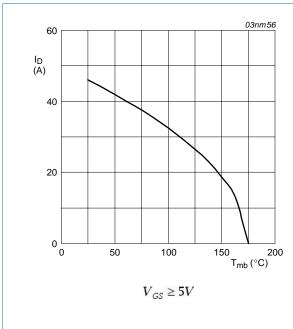


Fig 1. Normalized continuous drain current as a function of mounting base temperature

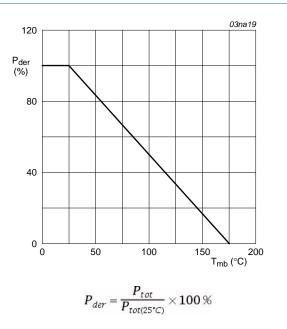
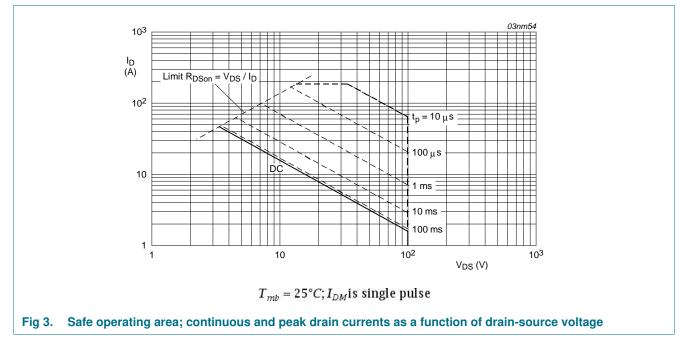


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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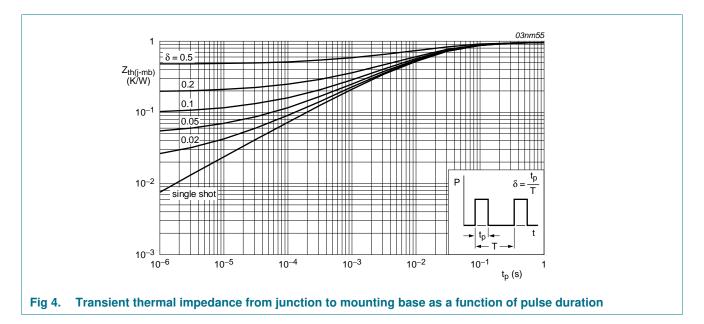
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	-	0.95	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 5</u>	1.1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 5</u>	-	-	2.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 5</u>	0.5	-	-	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I _{GSS}	gate leakage current	V_{GS} = 15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		$V_{GS} = -15 \text{ V}; \text{ V}_{DS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	32	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 6</u> ; see <u>Figure 7</u>	-	-	75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _i = 25 °C	-	22	27	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 6; see Figure 7	-	24	29	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$	-	33	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 8</u>	-	7	-	nC
Q _{GD}	gate-drain charge		-	13	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	3270	4360	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 9</u>	-	236	283	pF
C _{rss}	reverse transfer capacitance		-	103	141	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	30	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	86	-	ns
t _{d(off)}	turn-off delay time		-	96	-	ns
t _f	fall time		-	46	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 \text{ °C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 \text{ °C}$	-	7.5	-	nH

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10

120

Label is V_{GS} (V)

 $I_D(A)$

80

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Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 10</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	114	-	ns
Qr	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	196	-	nC

60

50

40

30

20

0

3.2

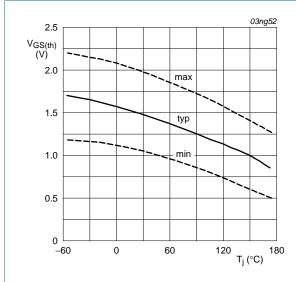
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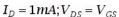
3.4

40

3.6 3.8

R_{DSon} (mΩ)







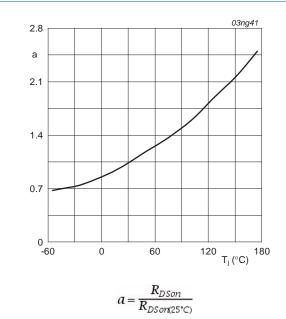


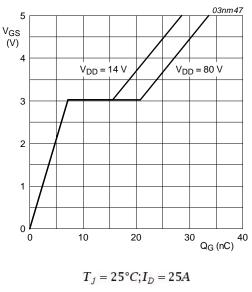
Fig 7. Normalized drain-source on-state resistance

factor as a function of junction temperature



Drain-source on-state resistance as a function

 $T_i = 25^{\circ}C$





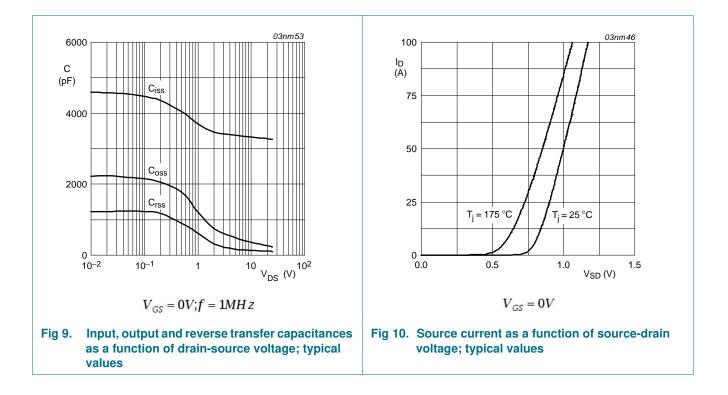
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7. Package outline

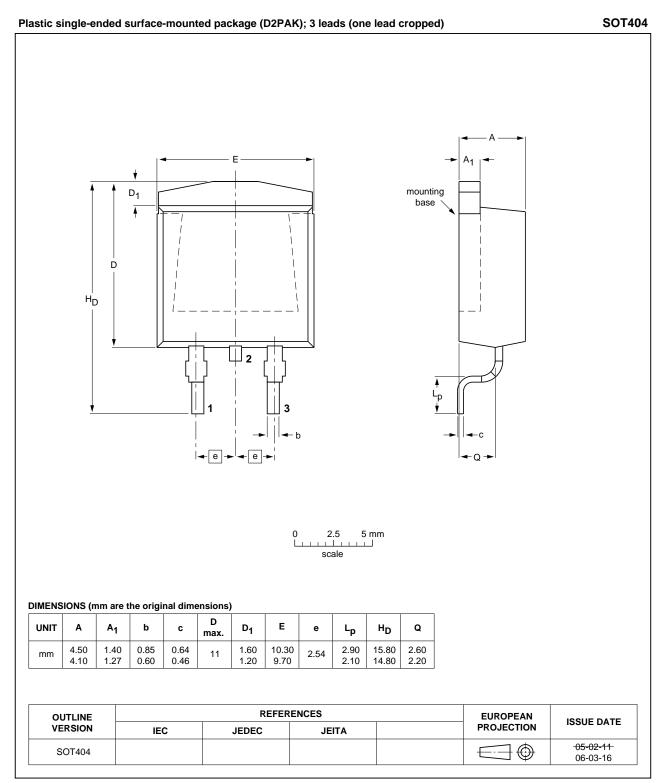


Fig 11. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9629-100B v.2	20110209	Product data sheet	-	BUK95_9629_100B v.1
Modifications:	 The format of this of NXP Semicon 		designed to comply wit	h the new identity guidelines
	 Legal texts have 	been adapted to the new	v company name whe	e appropriate.
	 Type number BL 	IK9629-100B separated	from data sheet BUK9	5_9629_100B v.1.
BUK95_9629_100B v.1 (9397 750 11249)	20030418	Product data	-	-

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9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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